



FDP150N10A_F102

N-Channel PowerTrench® MOSFET

100V, 50A, 15mΩ

Features

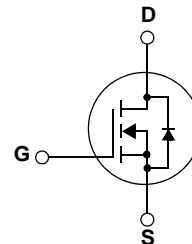
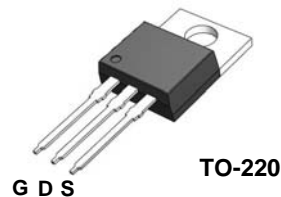
- $R_{DS(on)} = 12.5m\Omega$ (Typ.) @ $V_{GS} = 10V, I_D = 50A$
- Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- High Power and Current Handling Capability
- RoHS Compliant

Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advance PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

- DC to DC Converters
- Synchronous Rectification for Telecommunication PSU
- Battery Charger
- AC motor drives and Uninterruptible Power Supplies
- Off-line UPS



MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

| Symbol | Parameter | FDP150N10A_F102 | Units |
|----------------|--|--------------------------------------|------------|
| V_{DSS} | Drain to Source Voltage | 100 | V |
| V_{GSS} | Gate to Source Voltage | ± 20 | V |
| I_D | Drain Current | - Continuous ($T_C = 25^\circ C$) | 50 |
| | | - Continuous ($T_C = 100^\circ C$) | 36 |
| I_{DM} | Drain Current | - Pulsed (Note 1) | 200 |
| E_{AS} | Single Pulsed Avalanche Energy | (Note 2) | 84.6 |
| dv/dt | Peak Diode Recovery dv/dt | (Note 3) | 6.0 |
| P_D | Power Dissipation | ($T_C = 25^\circ C$) | 91 |
| | | - Derate above $25^\circ C$ | 0.61 |
| T_J, T_{STG} | Operating and Storage Temperature Range | -55 to +175 | $^\circ C$ |
| T_L | Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds | 300 | $^\circ C$ |

Thermal Characteristics

| Symbol | Parameter | Ratings | Units |
|-----------------|---|---------|--------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 1.6 | $^\circ C/W$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 62.5 | |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|-----------------|---------|-----------|------------|----------|
| FDP150N10A | FDP150N10A_F102 | TO-220 | - | - | 50 |

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Units |
|--------|-----------|-----------------|------|------|------|-------|
|--------|-----------|-----------------|------|------|------|-------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|---|-----|------|-----------|---------------------------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ | 100 | - | - | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\mu\text{A}$, Referenced to 25°C | - | 0.08 | - | $\text{V}/^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 80\text{V}, V_{GS} = 0\text{V}$ $V_{DS} = 80\text{V}, T_C = 150^\circ\text{C}$ | - | - | 1 500 | μA |
| I_{GSS} | Gate to Body Leakage Current | $V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$ | - | - | ± 100 | nA |

On Characteristics

| | | | | | | |
|--------------|--------------------------------------|--|-----|------|------|------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ | 2.0 | - | 4.0 | V |
| $R_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = 10\text{V}, I_D = 50\text{A}$ | - | 12.5 | 15.0 | $\text{m}\Omega$ |
| g_{FS} | Forward Transconductance | $V_{DS} = 10\text{V}, I_D = 50\text{A}$ (Note 4) | - | 40 | - | S |

Dynamic Characteristics

| | | | | | | |
|---------------|------------------------------------|--|-------------|------|------|----------|
| C_{iss} | Input Capacitance | $V_{DS} = 50\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$ | - | 1080 | 1440 | pF |
| C_{oss} | Output Capacitance | | - | 267 | 355 | pF |
| C_{rss} | Reverse Transfer Capacitance | | - | 11 | - | pF |
| $C_{oss(er)}$ | Energy Related Output Capacitance | $V_{DS} = 50\text{V}, V_{GS} = 0\text{V}$ | - | 436 | - | pF |
| $Q_{g(tot)}$ | Total Gate Charge at 10V | $V_{DS} = 50\text{V}, V_{GS} = 10\text{V}$ $I_D = 50\text{A}$ | - | 16.2 | 21.0 | nC |
| Q_{gs} | Gate to Source Gate Charge | | - | 5.3 | - | nC |
| Q_{gs2} | Gate Charge Threshold to Plateau | | - | 2.6 | - | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | (Note 4, 5) | - | 3.7 | - |
| ESR | Equivalent Series Resistance (G-S) | Drain Open, $f = 1\text{MHz}$ | - | 1.3 | - | Ω |

Switching Characteristics

| | | | | | | |
|--------------|---------------------|---|-------------|----|----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 50\text{V}, I_D = 50\text{A}$ $V_{GS} = 10\text{V}, R_{GEN} = 4.7\Omega$ | - | 13 | 36 | ns |
| t_r | Turn-On Rise Time | | - | 16 | 42 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | - | 21 | 52 | ns |
| t_f | Turn-Off Fall Time | | (Note 4, 5) | - | 5 | 20 |

Drain-Source Diode Characteristics

| | | | | | | |
|----------|--|--|---|-----|-----|----|
| I_S | Maximum Continuous Drain to Source Diode Forward Current | - | - | 50 | A | |
| I_{SM} | Maximum Pulsed Drain to Source Diode Forward Current | - | - | 200 | A | |
| V_{SD} | Drain to Source Diode Forward Voltage | $V_{GS} = 0\text{V}, I_{SD} = 50\text{A}$ | - | - | 1.3 | V |
| t_{rr} | Reverse Recovery Time | $V_{GS} = 0\text{V}, V_{DD} = 50\text{V}, I_{SD} = 50\text{A}$ | - | 50 | - | ns |
| Q_{rr} | Reverse Recovery Charge | $di_F/dt = 100\text{A}/\mu\text{s}$ (Note 4) | - | 55 | - | nC |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 2\text{mH}, I_{AS} = 9.2\text{A}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 100\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Dual Cycle $\leq 2\%$
5. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

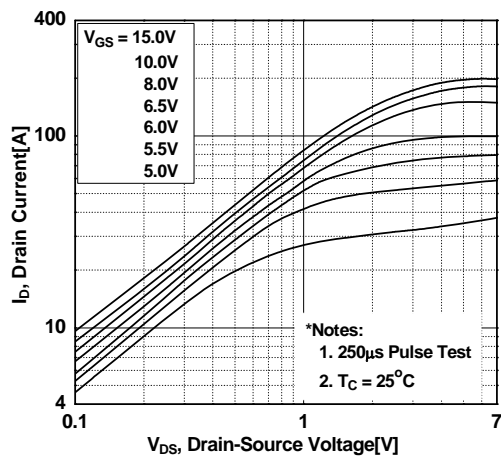


Figure 2. Transfer Characteristics

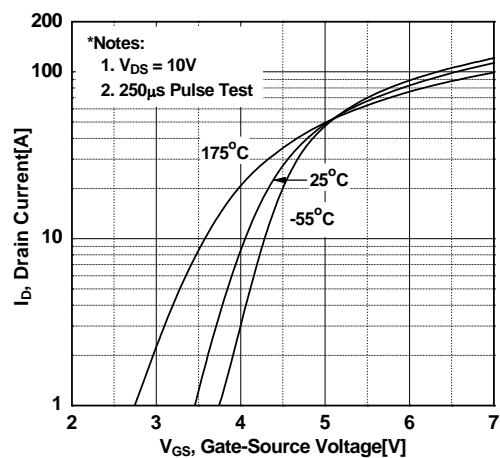


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

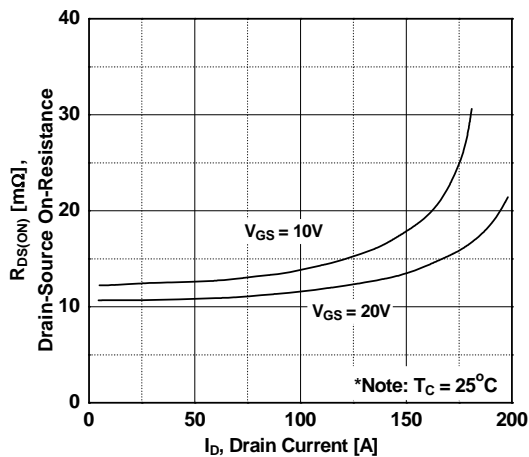


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

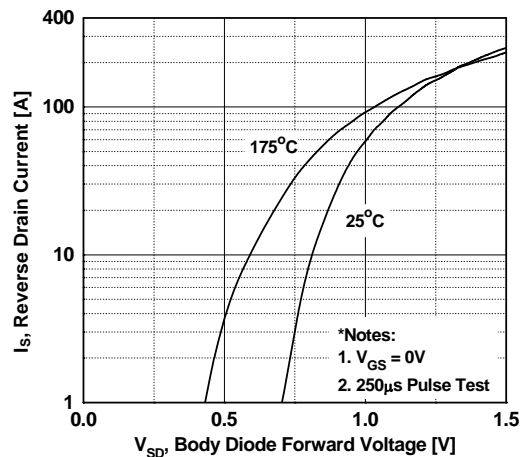


Figure 5. Capacitance Characteristics

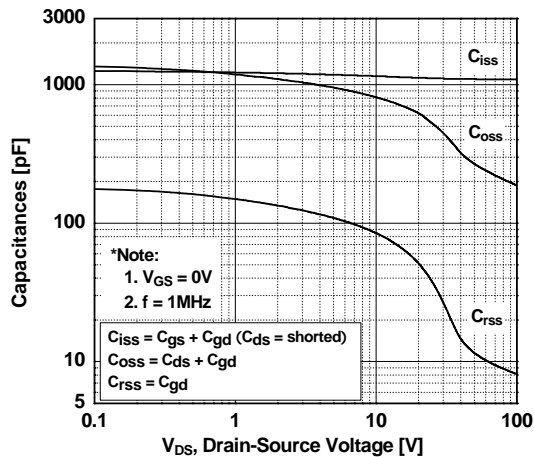
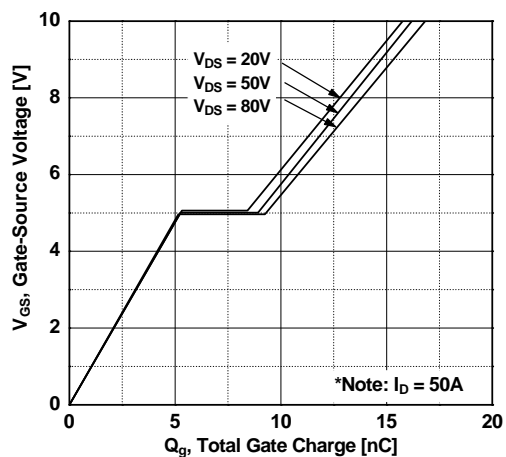


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

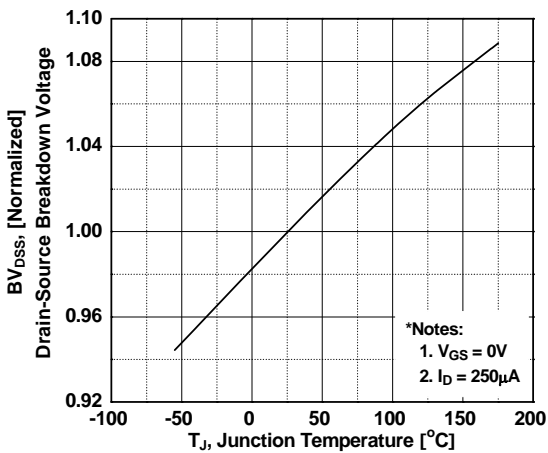


Figure 8. On-Resistance Variation vs. Temperature

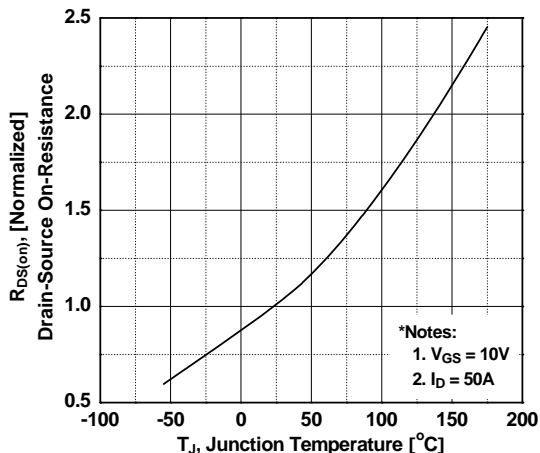


Figure 9. Maximum Safe Operating Area vs. Case Temperature

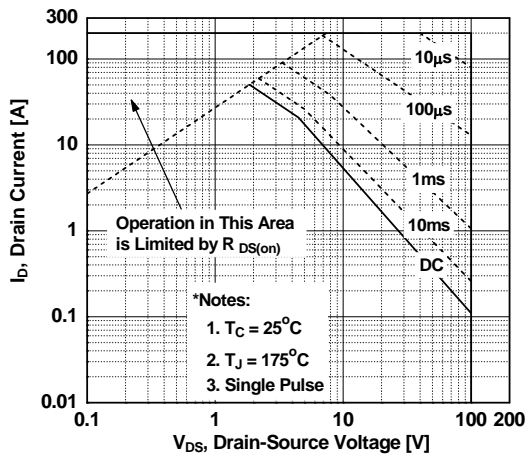


Figure 10. Maximum Drain Current

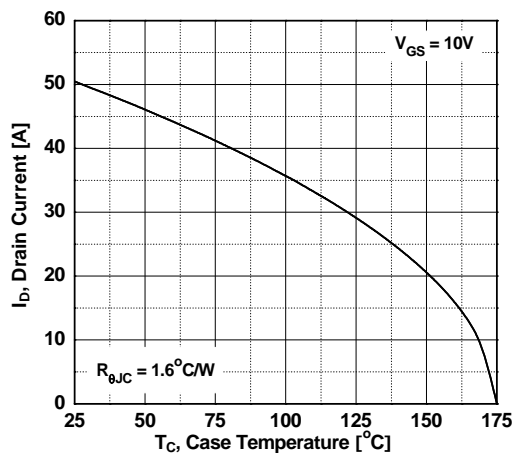


Figure 11. E_oss vs. Drain to Source Voltage

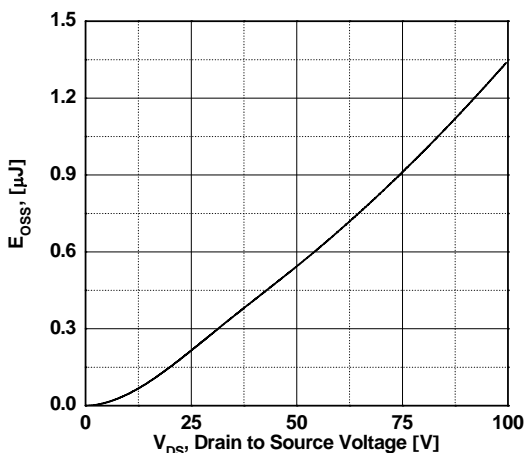
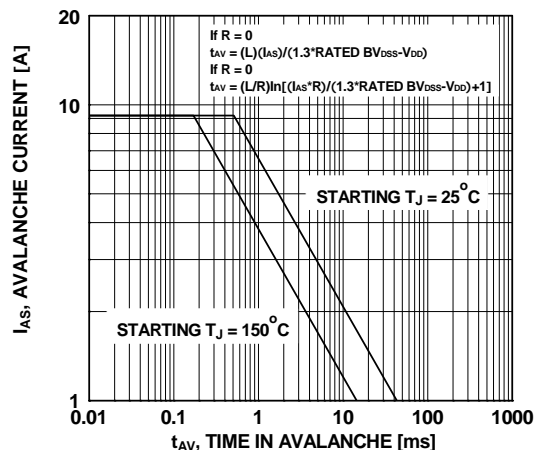
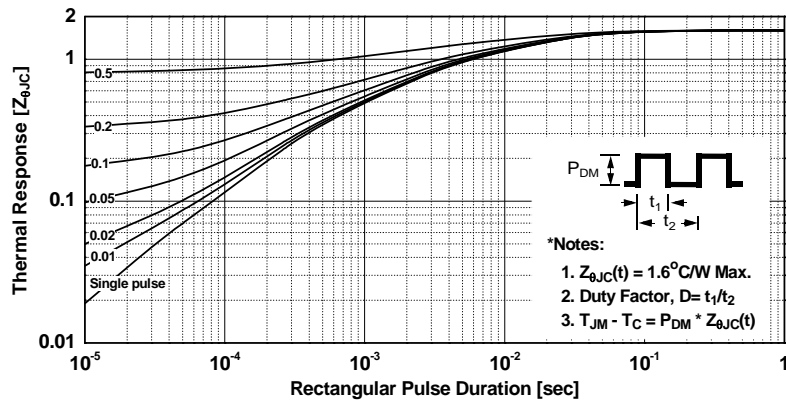


Figure 12. Unclamped Inductive Switching Capability

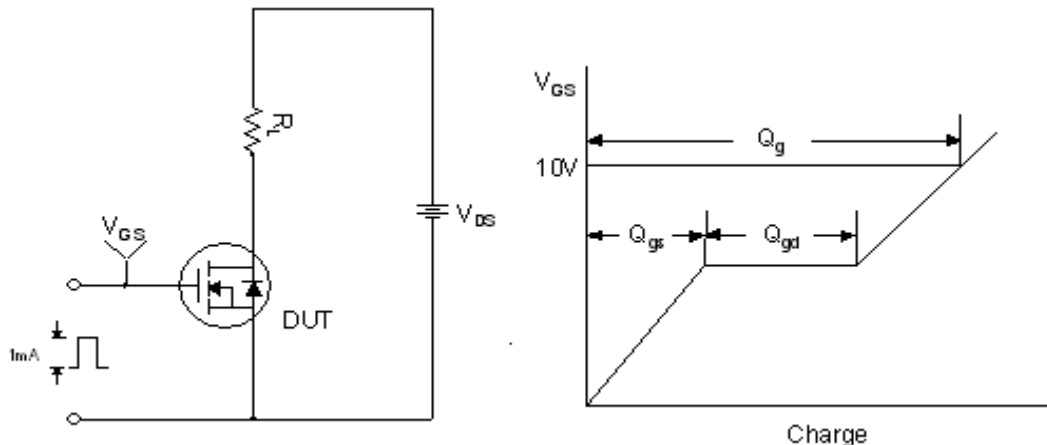


Typical Performance Characteristics (Continued)

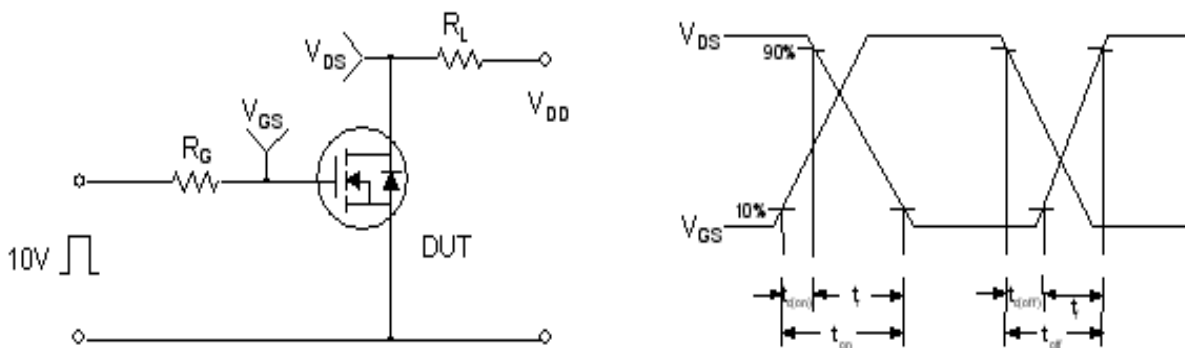
Figure 13. Transient Thermal Response Curve



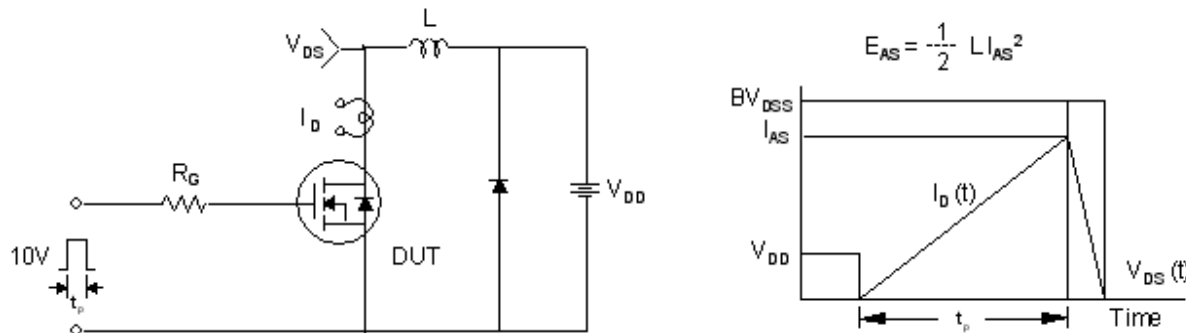
Gate Charge Test Circuit & Waveform



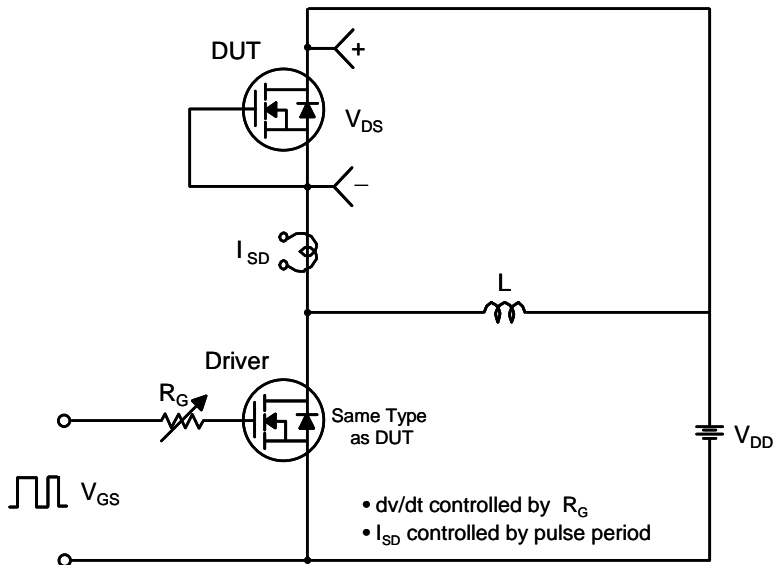
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

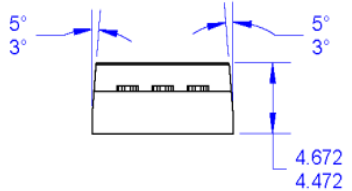
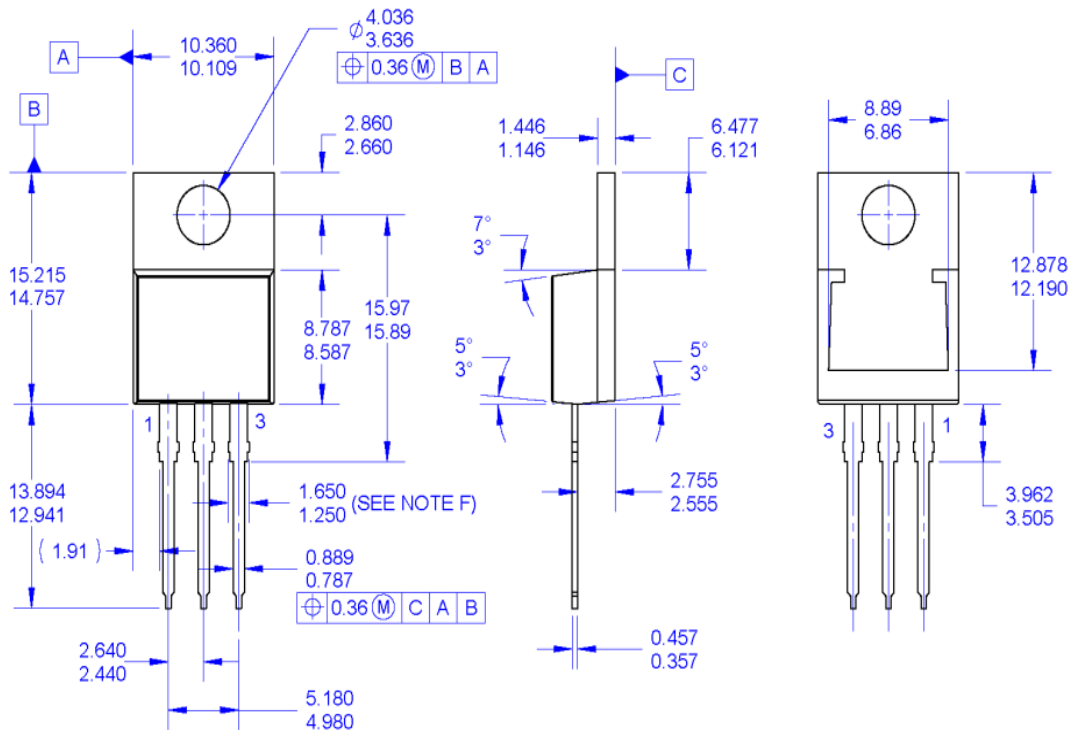


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

TO-220





NOTES:

- A. PACKAGE REFERENCE: JEDEC TO220 VARIATION AB
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. THIS PACKAGE IS FSZZ INTERNAL PRODUCTION AND INTENDED FOR DELTA CUSTOMER ONLY.
- F. MAX WIDTH FOR F102 DEVICE = 1.35mm.
- G. DRAWING FILE NAME: TO220T03REV2



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